



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE  
(Case No. 211.001-D4-US)

In the Application of: **Fazan et al.**

) Group Art Unit:

Serial No: **10/727,742**

) Before Examiner

Filed: **December 4, 2003**

)

Title: **Semiconductor Device**

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Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

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Michiko Steinberg  
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### FIRST INFORMATION DISCLOSURE STATEMENT

Dear Sir:

Submitted herewith are twenty-three (23) sheets of a modified Form PTO-1449.

The documents listed on the modified Form PTO-1449 were provided or cited during the prosecution of parent applications of the above-captioned application are not enclosed herewith. (See 37 C.F.R. §1.98(d) and MPEP 609). Should the Examiner desire an additional copy of the documents previously provided or cited during the prosecution of parent applications, kindly contact the undersigned.

It is respectfully requested that the Examiner make his/her consideration of these references formally of record with the initial Office Action.

Respectfully submitted,

Neil A. Steinberg  
Reg. No. 34,735  
650-968-8079

Date: March 12, 2004



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| U. S. DEPARTMENT OF COMMERCE<br>PATENT AND TRADEMARK OFFICE<br><br>INFORMATION DISCLOSURE STATEMENT<br>BY APPLICANT | ATTY. DOCKET NO.             | SERIAL NUMBER |
|   | 211.001-D4-US                | 10/727,742    |
|   | APPLICANT(S)<br>Fazan et al. |               |
| FILING DATE   | GROUP ART UNIT               |               |
| December 4, 2003  |                              |               |

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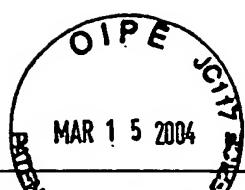
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